

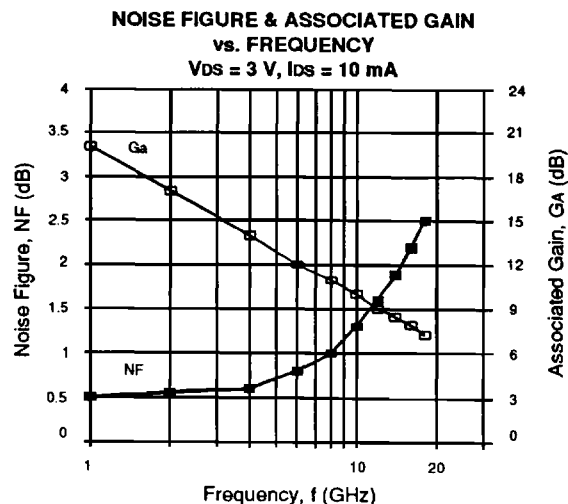
FEATURES

- **LOW NOISE FIGURE**
NF = 1.6 dB TYP at $f = 12$ GHz
- **HIGH ASSOCIATED GAIN**
GA = 9 dB TYP at $f = 12$ GHz
- **$L_g = 0.3 \mu\text{m}$, $W_g = 280 \mu\text{m}$**
- **ION IMPLANTATION**

DESCRIPTION

The NE76000 provides a low noise figure and high associated gain through K-Band. The NE760 devices are fabricated by ion implantation for improved RF and DC performance, reliability, and uniformity. These devices feature a recessed 0.3 micron gate and triple epitaxial technology. The surface of the device, except for bonding pads, is passivated with SiO_2 and SiN_4 for scratch protection as well as surface stability.

NEC's stringent quality assurance and test procedures assure the highest reliability and performance.



ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$)

PART NUMBER PACKAGE OUTLINE			NE76000 00 (CHIP)			NE76000L 00 (CHIP)		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX	MIN	TYP	MAX
NFOPT ¹	Optimum Noise Figure at $V_{DS} = 3 \text{ V}$, $I_{DS} = 10 \text{ mA}$, $f = 4 \text{ GHz}$ $f = 12 \text{ GHz}$	dB dB		0.6 1.6	1.8		1.8	
GA ¹	Associated Gain at $V_{DS} = 3 \text{ V}$, $I_{DS} = 10 \text{ mA}$, $f = 4 \text{ GHz}$ $f = 12 \text{ GHz}$	dB dB	8.0	13.0 9.0			8.0	
P _{1dB}	Output Power at 1 dB Compression, $V_{DS} = 3 \text{ V}$, $I_{DS} = 10 \text{ mA}$, $f = 12 \text{ GHz}$	dBm		14.5				
I_{DS}	Saturated Drain Current at $V_{DS} = 3 \text{ V}$, $V_{GS} = 0$	mA	15	30	50	50		80
V_P	Pinch-off Voltage at $V_{DS} = 3 \text{ V}$, $I_{DS} = 0.1 \text{ mA}$	V	-3.0	-0.8	-0.5	-3.0	-0.8	-0.5
gm	Transconductance, $V_{DS} = 3 \text{ V}$, $I_{DS} = 10 \text{ mA}$	mS	30.0	40.0			30.0	
I_{GSO}	Gate to Source Leakage Current, $V_{GS} = -4 \text{ V}$	μA		1.0	10.0		1.0	
$R_{TH} (\text{CH-C})^2$	Thermal Resistance (Channel to Case)	$^\circ\text{C/W}$			190			190

Notes:

1. RF performance is determined by packaging and testing 10 samples per wafer; wafer rejection criteria for standard devices is 2 rejects for 10 samples.
2. Chip mounted on infinite heat sink.

ABSOLUTE MAXIMUM RATINGS¹ ($T_A = 25^\circ\text{C}$)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V_{DS}	Drain to Source Voltage	V	5
V_{GD}	Gate to Drain Voltage	V	-5
V_{GS}	Gate to Source Voltage	V	-3
I_{DS}	Drain Current	mA	I_{DSS}
PIN	RF Input (CW)	dBm	+15
T_{CH}	Channel Temperature	$^\circ\text{C}$	175
T_{STG}	Storage Temperature	$^\circ\text{C}$	-65 to +175
P_{T2}	Total Power Dissipation	mW	240

Notes:

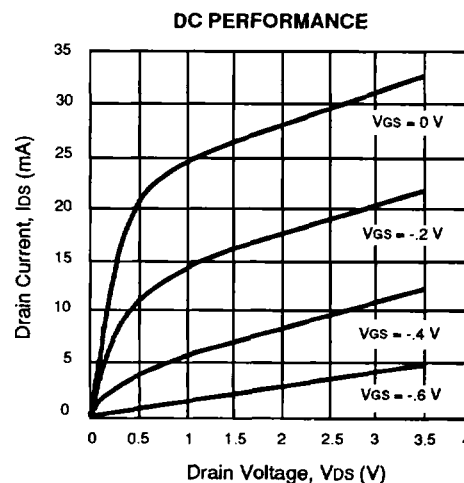
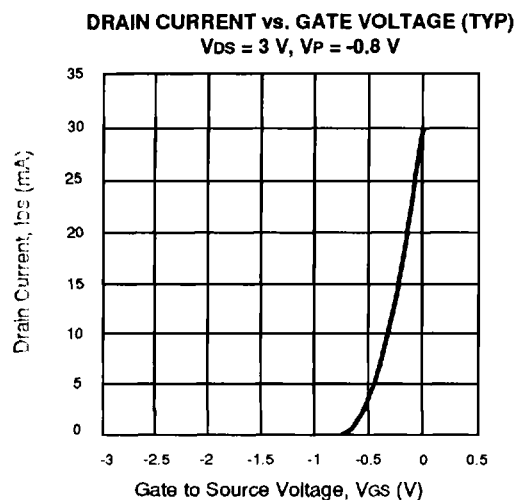
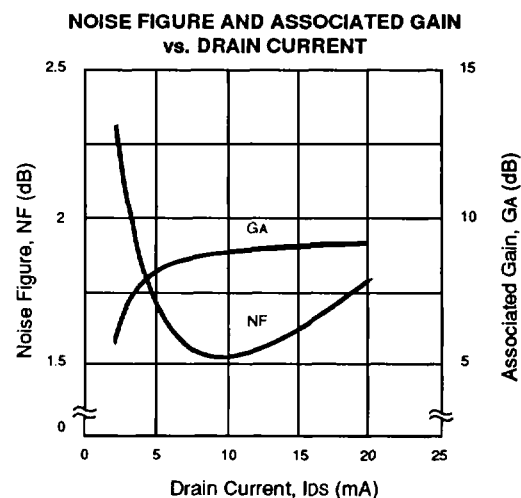
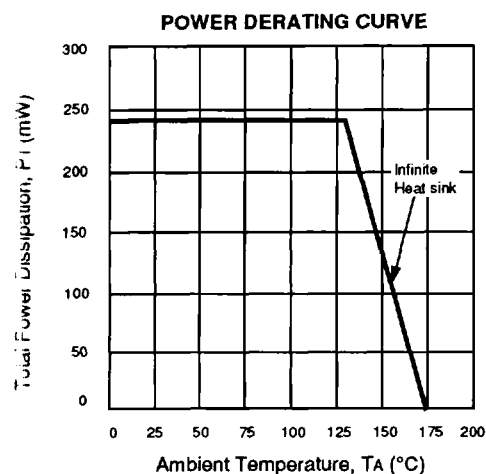
- Operation in excess of any one of these parameters may result in permanent damage.
- With chip mounted on a copper heat sink.

TYPICAL NOISE PARAMETERS¹($V_{DS} = 3.0$, $I_{DS} = 10$ mA)

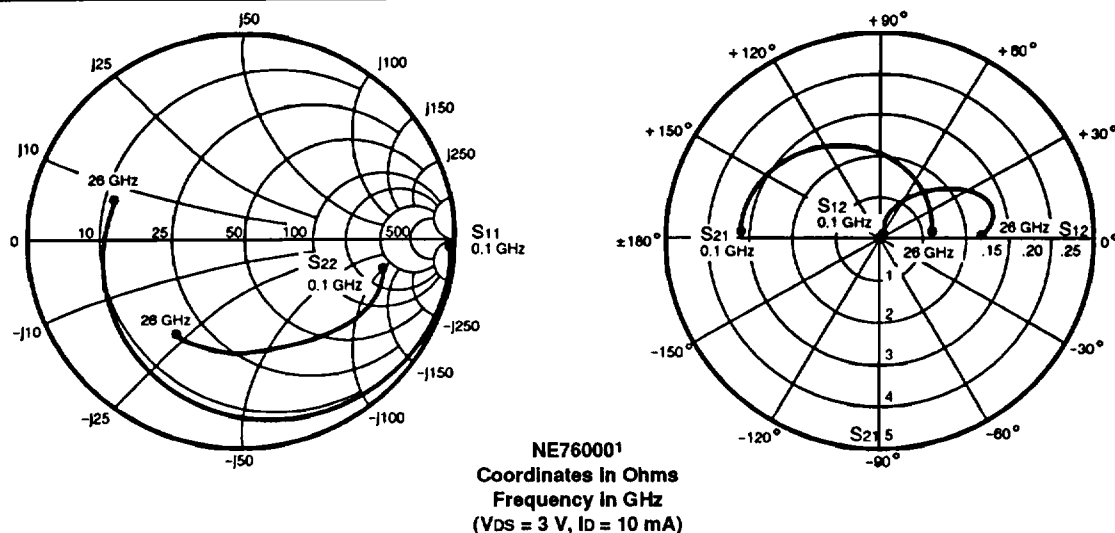
FREQ. (GHz)	NF _{OPT} (dB)	GA (dB)	Γ_{OPT}		Rn/50
			MAG	ANG	
1	0.50	20	.84	12	.69
2	0.55	17	.76	25	.63
4	0.60	14	.70	45	.49
6	0.80	12	.64	65	.41
8	1.00	11	.60	83	.36
10	1.30	10	.56	99	.32
12	1.60	9	.52	114	.27
14	1.90	8.5	.49	125	.23
16	2.20	7.9	.48	135	.20
18	2.50	7.3	.47	145	.18

Note:

- Noise parameters include bond wires:
 Gate: 2 wires total, 1 per bond pad, 0.0139" long each wire.
 Drain: 2 wires total, 1 per bond pad, 0.0115" long each wire.
 Sources: 4 wires total, 2 per side, 0.0066" long each wire.
 Wire: 0.0007" diameter, gold.

TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)

TYPICAL COMMON SOURCE SCATTERING PARAMETERS



VDS = 3 V, ID = 10 mA

FREQUENCY (GHz)	S11		S21		S12		S22		K	S21 (dB)	MAG ² (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG			
0.1	0.999	-2.0	3.291	179.0	0.002	90.0	0.677	-1.0	0.062	10.3	32.1
0.2	0.999	-3.0	3.282	178.0	0.004	89.0	0.677	-2.0	0.024	10.3	29.1
0.5	0.998	-7.0	3.280	175.0	0.010	85.0	0.675	-4.0	0.038	10.3	25.1
1.0	0.996	-13.0	3.265	169.0	0.020	81.0	0.673	-8.0	0.05	10.2	22.1
1.5	0.993	-20.0	3.218	164.0	0.030	78.0	0.671	-12.0	0.04	10.1	20.3
2.0	0.985	-27.0	3.185	158.0	0.039	74.0	0.666	-16.0	0.07	10.0	19.1
3.0	0.969	-39.0	3.079	148.0	0.057	66.0	0.655	-23.0	0.12	9.7	17.3
4.0	0.947	-50.0	2.950	138.0	0.072	59.0	0.640	-30.0	0.17	9.3	16.1
5.0	0.923	-61.0	2.814	129.0	0.085	51.0	0.621	-36.0	0.24	8.9	15.1
6.0	0.890	-70.0	2.669	120.0	0.094	47.0	0.602	-42.0	0.30	8.5	14.5
7.0	0.874	-78.0	2.545	113.0	0.104	41.0	0.590	-47.0	0.34	8.1	13.8
8.0	0.855	-87.0	2.446	104.0	0.110	36.0	0.579	-53.0	0.38	7.7	13.4
9.0	0.825	-96.0	2.328	97.0	0.114	30.0	0.565	-58.0	0.45	7.3	13.1
10.0	0.808	-104.0	2.237	90.0	0.119	29.0	0.565	-63.0	0.45	6.9	12.7
12.0	0.766	-120.0	2.077	76.0	0.132	19.0	0.558	-73.0	0.52	6.3	11.9
14.0	0.741	-135.0	1.926	63.0	0.134	12.0	0.549	-81.0	0.59	5.6	11.5
16.0	0.723	-147.0	1.800	53.0	0.134	6.0	0.553	-88.0	0.64	5.1	11.2
18.0	0.700	-155.0	1.653	43.0	0.130	3.0	0.530	-94.0	0.80	4.3	11.0
20.0	0.677	-162.0	1.528	35.0	0.121	4.0	0.519	-99.0	0.98	3.6	11.0
22.0	0.665	-171.0	1.464	26.0	0.115	4.0	0.520	-107.0	1.08	3.3	9.3
24.0	0.638	178.0	1.390	16.0	0.121	5.0	0.537	-116.0	1.08	2.8	8.8
26.0	0.616	164.0	1.286	7.0	0.123	4.0	0.538	-123.0	1.18	2.1	7.5

Notes:

1. S-parameters include bond wires.

Gate: Total 2 wire (s), 1 per bond pad, 0.0139" (354 μm) long each wire.

Drain: Total 2 wire(s), 1 per bond pad, 0.0115" (291 μm) long each wire.

Source: Total 4 wire (s), 2 per side, 0.0066" (168 μm) long each wire.

Wire: 0.0007" (17.8 μm) Diameter, Gold.

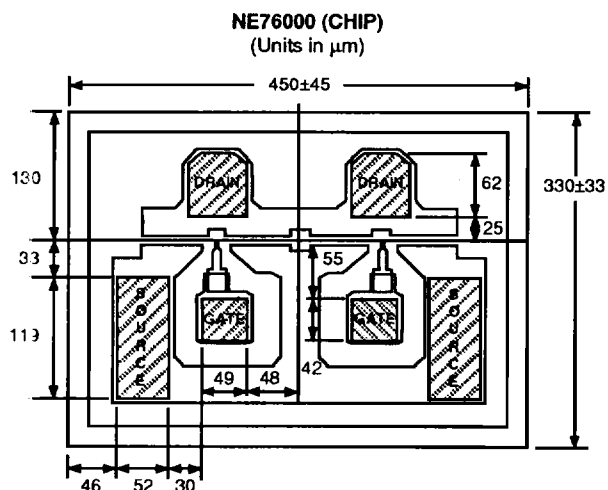
2. Gain Calculations:

$$\text{MAG} = \frac{|S_{21}|}{|S_{12}|} \left(K \pm \sqrt{K^2 - 1} \right) \quad \text{When } K \leq 1, \text{ MAG} = \text{MSG.} \quad \text{MSG} = \frac{|S_{21}|}{|S_{12}|}, \quad K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12} S_{21}|}, \quad \Delta = S_{11} S_{22} - S_{21} S_{12}$$

MAG = Maximum Available Gain

MSG = Maximum Stable Gain

OUTLINE DIMENSIONS (Units in mm)



 Bonding Pad Area Chip Thickness: $140\mu\text{m}\pm 20\mu\text{m}$

Not: All dimensions are typical unless otherwise stated.

ORDERING INFORMATION

PART NUMBER	IDSS SELECTION (mA)
NE76000L	50 to 80
NE76000N	15 to 50